



Features

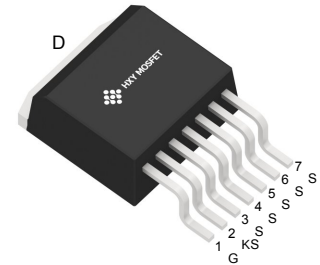
- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant

Benefits

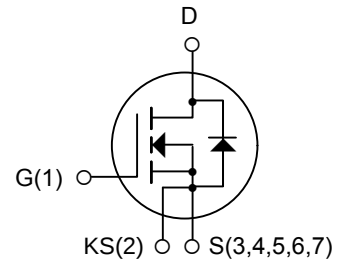
- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

Applications

- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



TO-263-7L



Ordering Part Number	Package	Brand
NVBG015N065SC1	TO-263-7L	HXY MOSFET

Maximum Ratings (T_c = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V _{DSmax}	Drain-Source Voltage	V _{GS} = 0V, I _D = 100μA	750	V	
V _{GS}	Gate-Source voltage (transient)	t _p ≤ 500ns, duty cycle ≤ 1%	-8/+20	V	
V _{GSop}	Recommend Gate-Source Voltage	Static	-4/+18	V	
I _D	Continuous Drain current	V _{GS} = 18V, T _C = 25°C	210	A	Fig. 14
		V _{GS} = 18V, T _C = 100°C	148		
I _{D,pulse}	Pulsed Drain Current	Pulse with t _p limited by T _{jmax}	503	A	
P _D	Power Dissipation	T _C = 25°C, T _j = 175°C	714	W	Fig.16
T _j	Operating junction temperature		-55~175	°C	
T _{stg}	Storage temperature		-55~175	°C	



Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		0.21		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

Electrical Characteristics (T_c = 25°C unless other wise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0V, I_D = 100\mu A$	750			V	
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 36mA$		2.8		V	Fig. 9
		$V_{GS} = V_{DS}, I_D = 36mA, T_j = 175^\circ C$		2.0			
I_{GSS}	Gate-Source Leakage current	$V_{GS} = 18V, V_{DS} = 0V$			250	nA	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 750V, V_{GS} = 0V, T_j = 25^\circ C$		1	50	μA	
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 18V, I_D = 80A$		11	15	m Ω	Fig. 3, 4, 5
		$V_{GS} = 18V, I_D = 80A, T_j = 175^\circ C$		14			
g_{fs}	Transconductance	$V_{DS} = 18V, I_D = 80A$		60		S	Fig. 6
		$V_{DS} = 18V, I_D = 80A, T_j = 175^\circ C$		54			



Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q_{GS}	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 80A$ $V_{GS} = -4V/18V$		84		nC	Fig. 10
Q_{GD}	Gate to Drain Charge			62			
Q_G	Total Gate Charge			235			

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1MHz$ $V_{AC} = 25mV$		5670		pF	Fig. 13
C_{oss}	Output Capacitance			383		pF	
C_{rss}	Reverse Transfer Capacitance			37		pF	
$R_{G(int)}$	Internal Gate Resistance	$f = 1 MHz, V_{AC} = 25mV$		1.2		Ω	



Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	$V_{GS} = -4V, I_{SD} = 40A$		3.9		V	Fig. 7,8
		$V_{GS} = -4V, I_{SD} = 40A, T_J = 175^{\circ}C$		3.4			
I_S	Continuous Diode Forward Current	$V_{GS} = -4V, T_C = 25^{\circ}C$		152		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4V$, pulse width t_p limited by T_{jmax}		503		A	
t_{rr}	Reverse Recovery Time	$V_{GS} = -4V, I_{SD} = 80A, V_R = 400V$ $diff/dt = 3000A/us$		22		nS	
Q_{rr}	Reverse Recovery Charge			335		nC	
I_{rm}	Peak Reverse Recovery Current			32		A	

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400V, V_{GS} = -4/+18V$ $I_D = 80A, R_{G(ext)} = 5\Omega$ $L = 100\mu H$		8		nS	Fig.21
t_r	Rise Time			35		nS	
$t_{d(off)}$	Turn-Off Delay Time			38		nS	
t_f	Fall Time			9		nS	
E_{on}	Turn-On Energy			222		μJ	Fig.19
E_{off}	Turn-Off Energy			370		μJ	
E_{tot}	Total switching energy			592		μJ	



Typical Performance

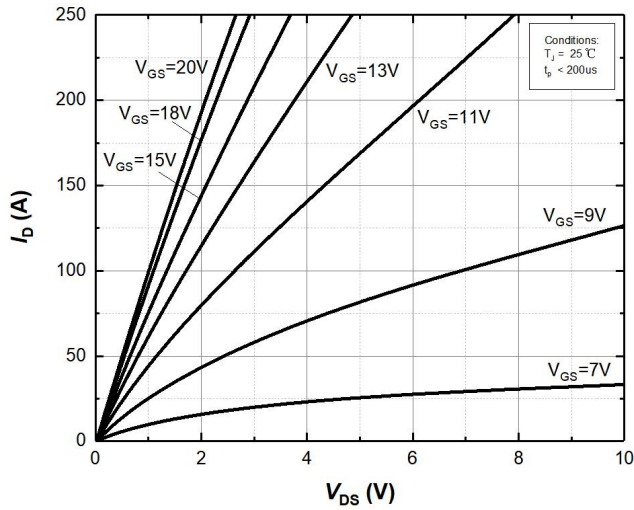


Figure 1. Output characteristics at $T_j=25^\circ\text{C}$

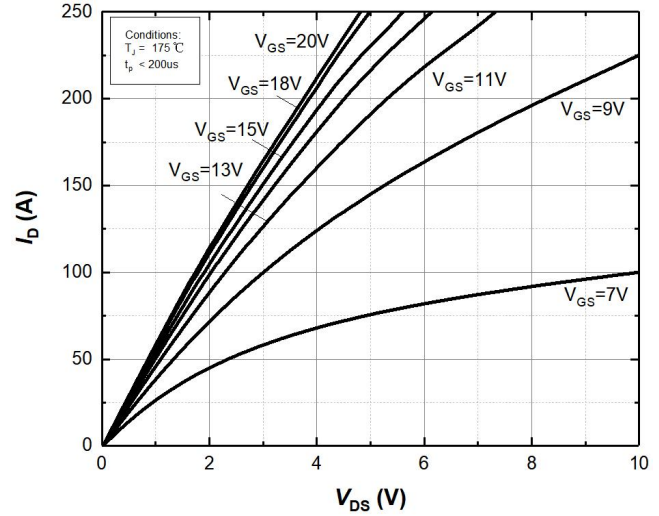


Figure 2. Output characteristics at $T_j=175^\circ\text{C}$

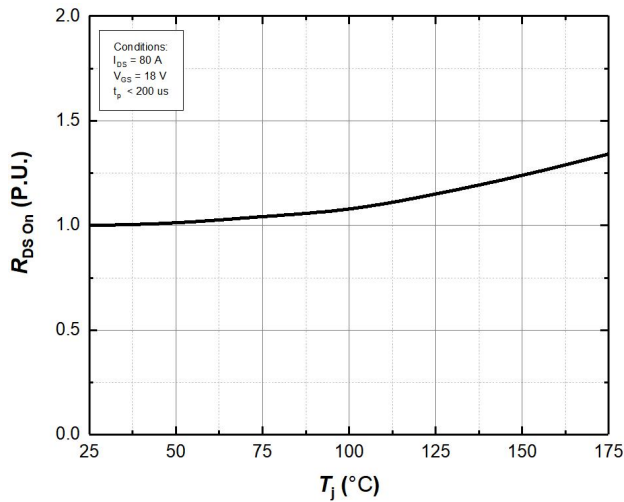


Figure 3. Normalized On-Resistance vs. Temperature

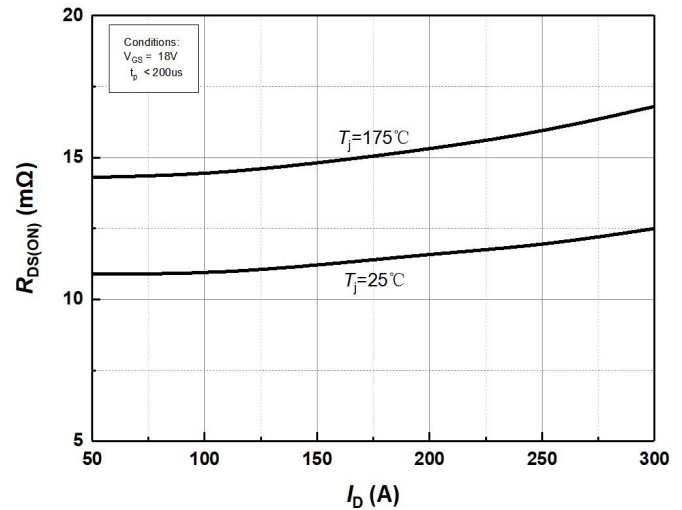


Figure 4. On-Resistance vs. Drain current for Various Temperature

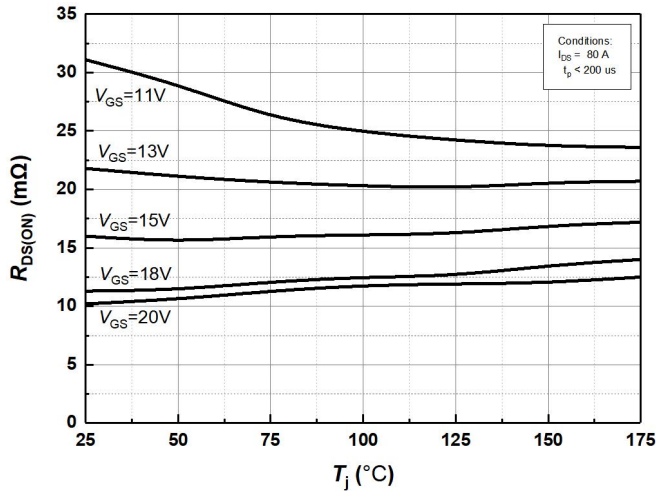


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

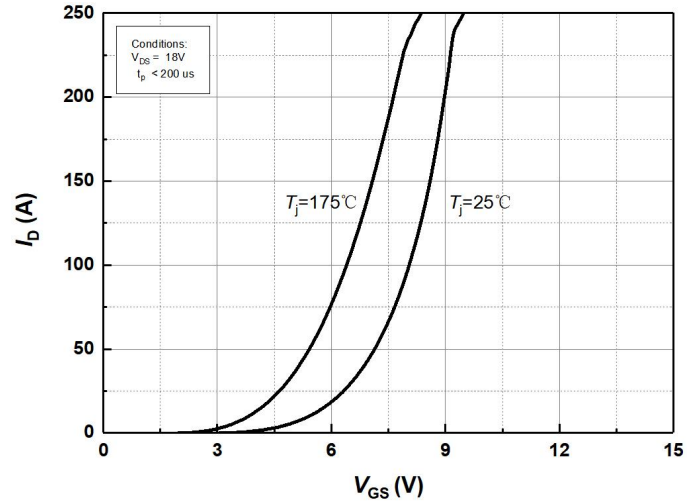


Figure 6. Transfer Characteristics for Various Junction Temperatures

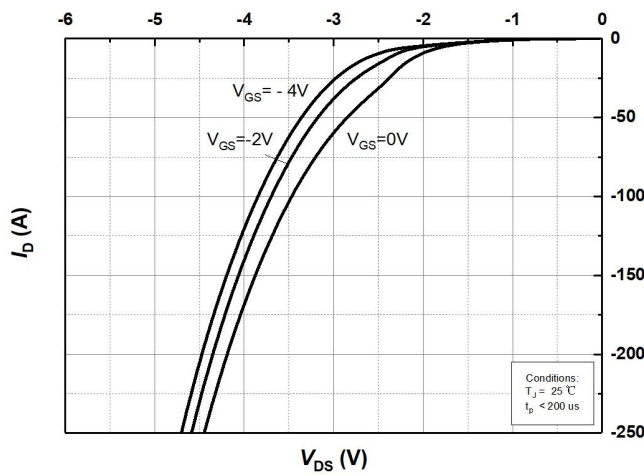


Figure 7. Body Diode Characteristics at $T_j=25^\circ\text{C}$

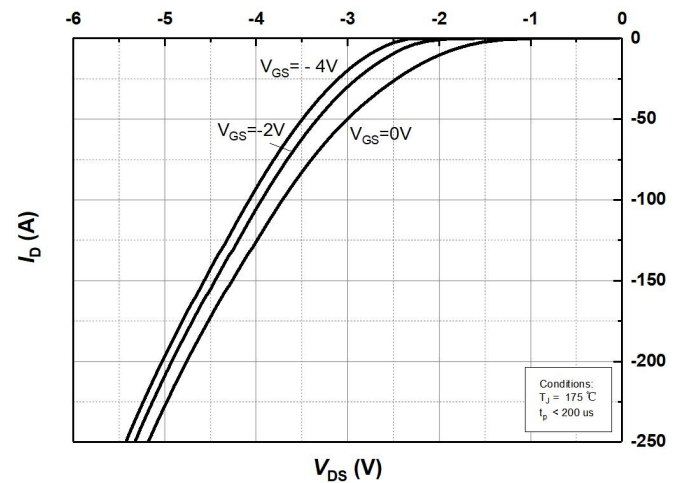


Figure 8. Body Diode Characteristics at $T_j=175^\circ\text{C}$

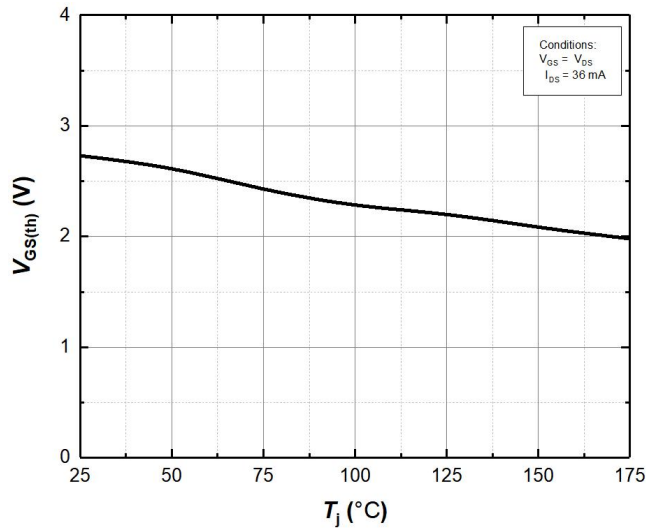


Figure 9. Threshold Voltage vs. Temperature

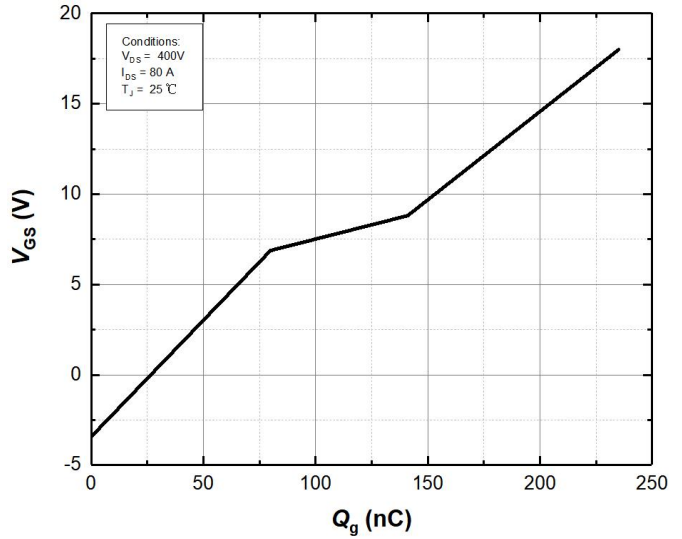


Figure 10 Gate Charge Characteristics

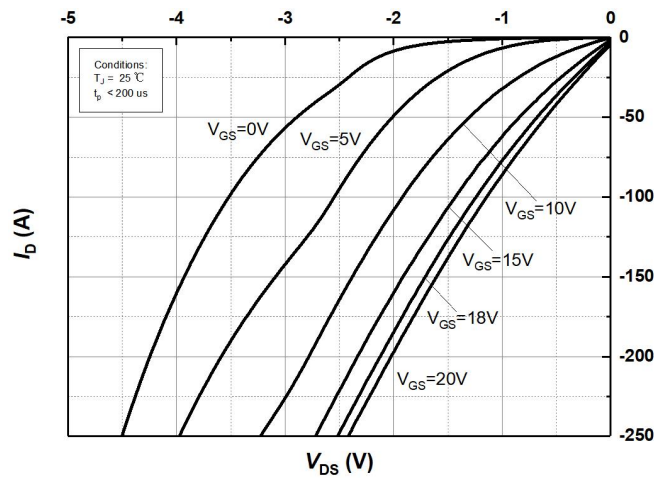


Figure 11. 3rd Quadrant Characteristic at $T_J=25\text{ °C}$

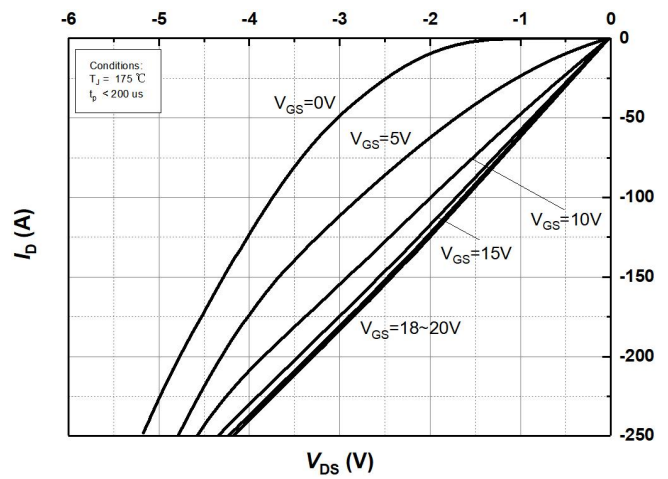


Figure 12. 3rd Quadrant Characteristic at $T_J=175\text{ °C}$

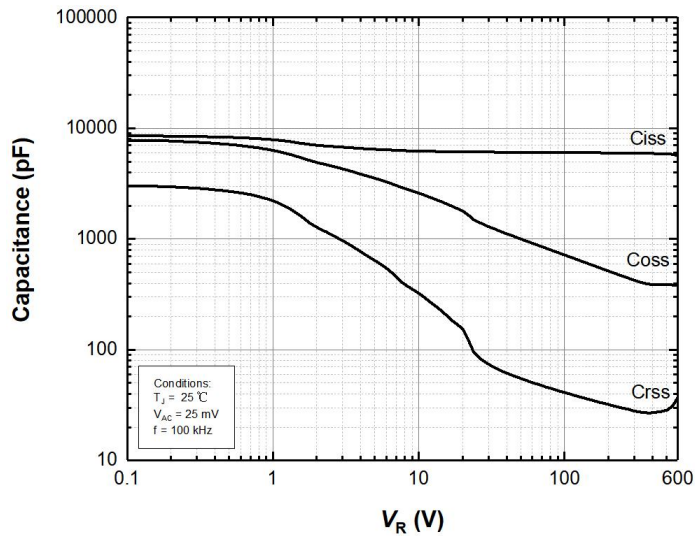


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

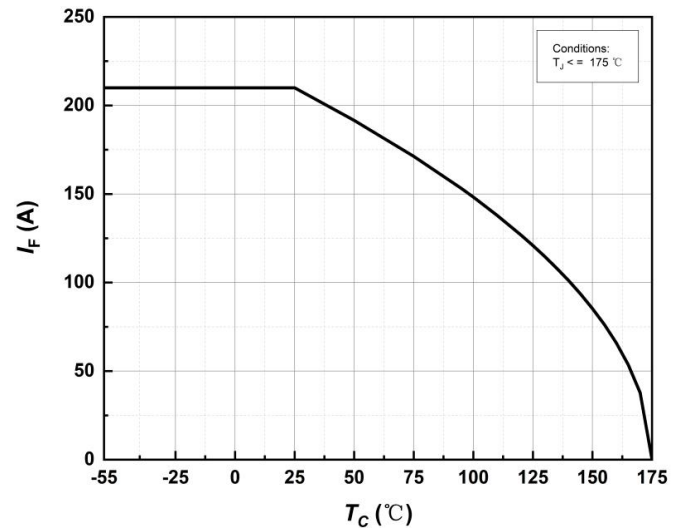


Figure 14. Continuous Drain Current Derating vs Case Temperature

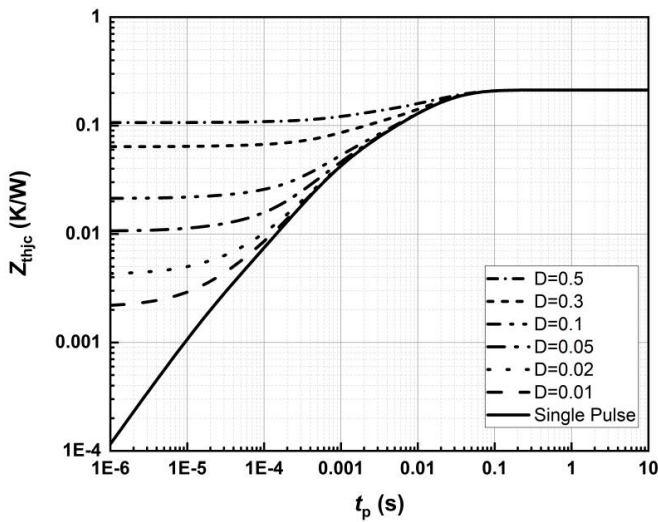


Figure 15. Transient Thermal Impedance (Junction – Case)

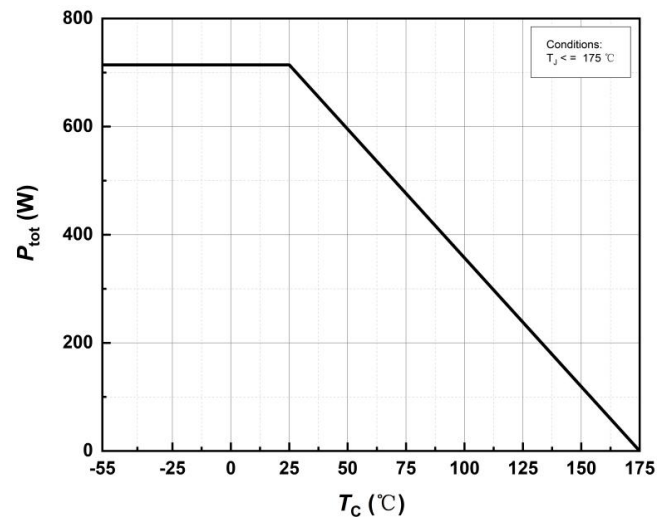


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

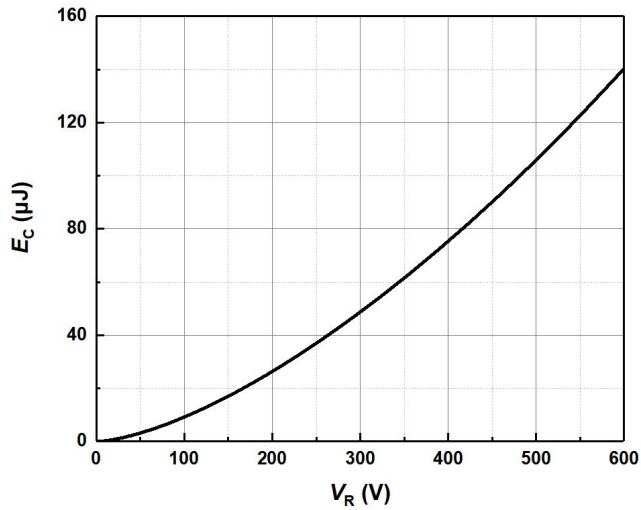


Figure 17. Output Capacitor Stored Energy

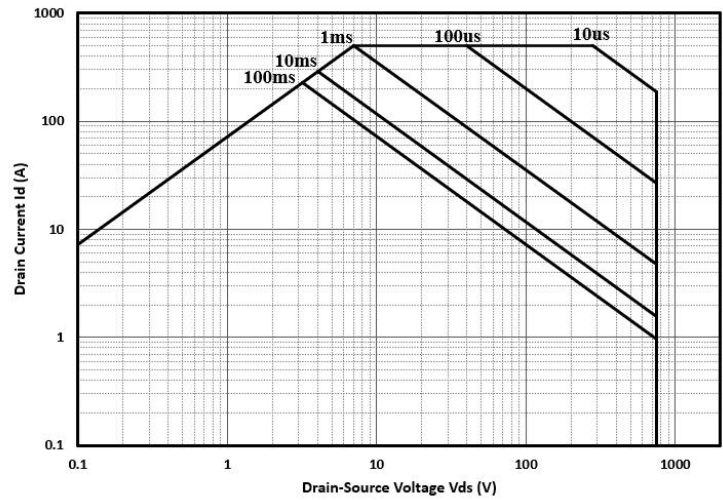


Figure 18. Safe Operating Area

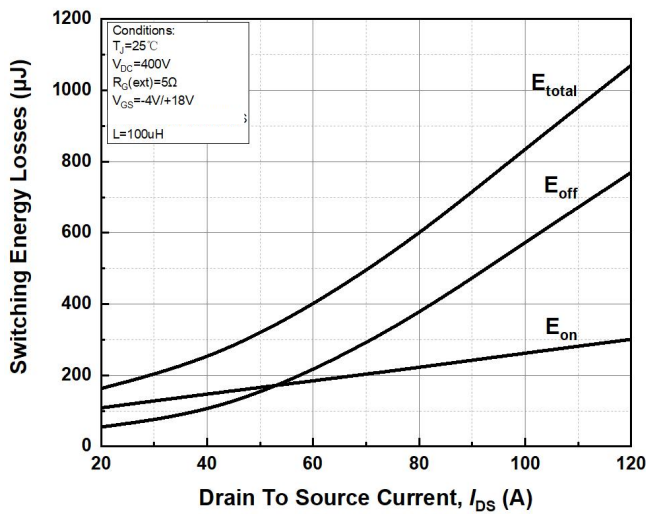


Figure 19. Clamped Inductive Switching Energy vs. Drain Current($V_{DD} = 400V$)

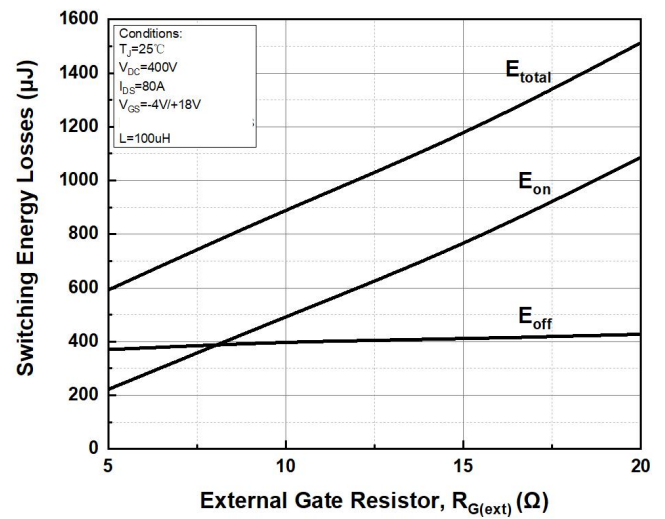


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

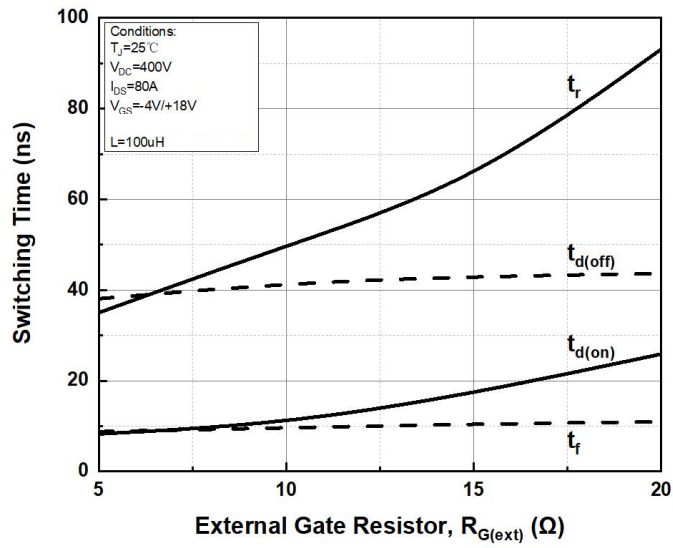
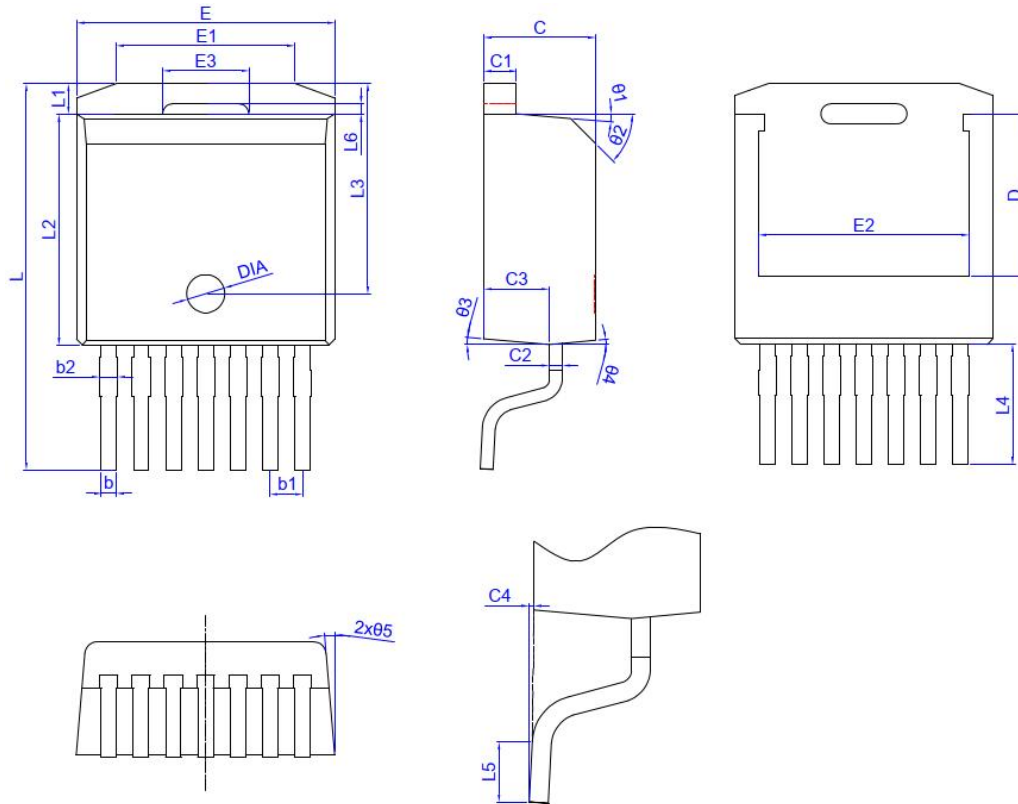


Figure 21. Switching Times vs. $R_{G(\text{ext})}$



Package Dimensions

Package TO-263-7L



标注	尺寸(mm)	MD测量	T&F测量
E	10.18±0.10		★
E1	7.00±0.20		★
E2	8.30±0.20	★	
E3	3.20±0.20		
L	15.20±0.25		
L1	1.20±0.25		★
L2	9.08±0.20	★	
L3	8.28±0.30		
L4	4.80±0.15		
L5	1.80±0.20		★
L6	0.40±0.05		
b	0.60±0.1		
b1	1.27±0.07		★
b2	0.7±0.1		★
C	4.43±0.15	★	
C1	1.30±0.1		
C2	0.50±0.07		
C3	2.60±0.15		★
C4	0 - 0.1		★
D	6.45±0.15	★	
θ1	5°±2°		
θ2	45°±2°		
θ3	5°±2°		
θ4	5°±2°		
θ5	5°±2°		
DIA	宽1.50±0.10 深0.05 - 0.45	★	

备注:

1. 标★尺寸为对应工序的关键测量尺寸;

2. L5 测量方法: 测量仪器的垂直定位线先与散热片重合后, 下移至于引脚处, 与引脚交点至引脚底端长度为 L5 测量值。



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